





1728 #11/10 3/1/3

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Appln. Of:

TANABE et al.

Serial No.:

09/612,551

Filed:

July 7, 2000

For:

SEMICONDUCTOR THIN FILM FORMING SYSTEM

Group:

1725

Examiner:

**GEOFFREY S. EVANS** 

DOCKET: NEC WNZ-2212

Assistant Commissioner of Patents and Trademarks Washington, D.C. 20231

## **AMENDMENT D**

Dear Sir:

The following Amendment is being filed in response to the Official Action mailed

December 5, 2002.

Please amend the Application as follows:

## **IN THE TITLE:**

Please amend the title to read as follows:

--A SYSTEM FOR THE FORMATION OF A SILICON THIN FILM AND A

SEMICONDUCTOR-INSULATING FILM INTERFACE--

## IN THE CLAIMS:

Please amend claims 1 and 17-22 to read as follows:

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175 CANAL STREET MANCHESTER, NH 03101 TEL. 603.668.1400 FAX. 603.668.8567 1. (Twice Amended) A semiconductor thin film forming method comprising:

modifying a predetermined region of a semiconductor thin film by exposing the

semiconductor thin film to a projected light patterned through plural patterns formed on a photo

mask; and